

Abstracts

Gunn Diode Power Combining at U-Band

Y. Ma and C. Sun. "Gunn Diode Power Combining at U-Band." 1980 MTT-S International Microwave Symposium Digest 80.1 (1980 [MWSYM]): 65-66.

A modular approach for combining many Gunn devices has been developed. By stacking simple two-diode wafer modules, output power of 620 mW was achieved at around 45 GHz from 6 Gunn devices with a combining efficiency of 86 percent. The locking bandwidth was about 200 MHz with 20 dB locking gain.

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